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| Objective |
| Batch name: Process template |
| This process flows is a guideline on how to spin, develop and rinse AZ5214E on substrates as Si, SiO2 and SOI, using the SSE Spin coater and Aligner-6inch or KS Aligner, in case you will do lift-off process. |

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| Step Heading | Equipment |  | Comments |
| 1. Pretreatment
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| * 1. Surface treatment
 | BHF dip *or*HMDSorTrack 1 or 2 | BHF dip for Si substrates (30 sec, H2O 5 min) HMDS treatment for SiO2 and III-V substratesRecipe: T1T2 HMDS only |  |
| 1. Spin coat of AZ5214E 1.5µm
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| * 1. Clean spinner
 | SSE spinner | Clean spinner nozzle and run the dummy wafersRecipe: 1.5 4inch | 1-3 dummiesNote time in logbook |
| * 1. Coat wafers
 | SSE Spinner | **Resist:** AZ5214E**Recipe:** 1,5um\_4inch or 1,5um\_6inch**Softbake:** Is included in the spinning recipe90sec@90deg  | Resist thickness can be measured on FilmTekRecipe: resist\_QC\_9points |
| 1. Exposure
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| * 1. Exposure
 | Aligner-6inchKS Alignment | **Recipe:** DCH\_1,5\_FPA\_rev in case you will not alignOr DCH\_1,5\_TSA in case you do a Top Side Alignment**Exposure mode:** Hard Contact**Exposure time:** 1,7 sec**Mask**: your mask**Reverse Bake:** ….**Exposure mode: Flood exposure****Exposure time: 30 sec****Exposure mode:** Hard Contact**Exposure time:** 3,5 sec**Mask**: your mask**Reverse Bake:** 100sec@110deg**Exposure mode: Flood exposure****Exposure time: 30 sec** | We suggest you do a dose test exposure to find an optimum exposure for your process.Remove your mask and do flood exposureUse 110deg HotPlate |
| 1. Development & Rinse
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| * 1. Develop
 | Developer bench orDeveloper-6inchDeveloper TMAH UV-lithography | Develop in 351B for 60±10 secDevelop in TMAH for 60 sec puddle | Rinse and spin dry included in developing recipe |
|  | Wet bench/ Spin dryer | Rinse in DI water for 5 min (300±30 sec).Spin dry |  |
| 1. Inspection
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| * 1. Inspection
 | Optical microscope | Check pattern and alignment marks | Optical microscope |